## DECLARATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name.

I believe I am the original, first and sole inventor (if only one name is listed below) or the below named inventors are the original, first and joint inventors (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled A METHOD OF FORMING A SUBSTRATE CONTACT IN A FIELD EFFECT TRANSISTOR FORMED OVER A BURIED INSULATOR LAYER, the Specification of which:

is attached hereto.

is attached hereto.

was filed on 31/10/2000 as Application Serial No. 100 54 109.7 in Germany.

I hereby state that I have reviewed and understand the contents of the above-identified specification, including the claims.

I acknowledge the duty to disclose to the Patent and Trademark Office all information known to me to be material to patentability of the subject matter claimed in this application, as "materiality" is defined in Title 37, Code of Federal Regulations, § 1.56.

I hereby claim priority benefits under Title 35, United States Code, § 119 and/or § 365 of any foreign application(s) for patent or inventor's certificate, PCT international application(s), and United States provisional application(s), listed below and have also identified below any foreign application for patent or inventor's certificate, PCT international application, or United States provisional application, having a filing date before that of the application on which priority is claimed:

	PRIORITY APPI	Priority Claimed	
100 54 109.7	Germany	31/10/2000	Yes
(Number)	(Country)	(Date Filed)	Yes/No
(Number)	(Country)	(Date Filed)	Yes/No

I hereby claim the benefit under Title 35, United States Code, § 120 and/or § 365 of any United States application(s) and PCT international application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT international application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose all information known to me to be material to patentability of the subject matter claimed in this application, as "materiality" is defined in Title 37, Code of Federal Regulations, § 1.56, which becomes available between the filing date of the prior application and the national or PCT international filing date of this application:

(Application Serial No.)	(Filing Date)	(Status)	
(Application Serial No.)	(Filing Date)	(Status)	

I hereby direct that all correspondence and telephone calls be addressed to , Williams, Morgan & Amerson, P.C., 7676 Hillmont, Suite 250, Houston, Texas 77040, (713) 934-7000.

I HEREBY DECLARE THAT ALL STATEMENTS MADE OF MY OWN KNOWLEDGE ARE TRUE AND THAT ALL STATEMENTS MADE ON INFORMATION AND BELIEF ARE BELIEVED TO BE TRUE; AND FURTHER THAT THESE STATEMENTS WERE MADE WITH THE KNOWLEDGE THAT WILLFUL FALSE STATEMENTS AND THE LIKE SO MADE ARE PUNISHABLE BY FINE OR IMPRISONMENT, OR BOTH, UNDER SECTION 1001 OF TITLE 18 OF THE UNITED STATES CODE AND THAT SUCH WILLFUL FALSE STATEMENTS MAY JEOPARDIZE THE VALIDITY OF THE APPLICATION OR ANY PATENT ISSUED THEREON.

Inventor's Full Name:	Gert	Burbach		
Inventor's Signature:	g . 7	alloll		
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## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Gert Burbach,
Frank Heinlein, Johannes
Groschopf, Gotthard Jungnickel,
Hartmut Ruelke & Carsten Hartig
Scrial No.: Unknown

Serial No.: Unknown

Filed: Concurrently Herewith

For: Method of Forming a Substrate
Contact in a Field Effect
Transistor Formed Over a
Buried Insulator Layer

POWER OF ATTORNEY

**Assistant Commissioner for Patents** 

Washington, D.C. 20231

Sir:

The undersigned, being the inventors named in the above-identified application, hereby revoke (revokes) any previous Powers of Attorney and appoint (appoints):

Elizabeth A. Apperley, Reg. No. 36,428; Paul S. Drake, Reg. No. 33,491; Richard J. Roddy, Reg. No. 27,688; Michael Caywood, Reg. No. 37,797; Bradley Botsch, Reg. No. 34,552; Harry A. Wolin, Reg. No. 32,638; and Raj Jaipershad, Reg. No. 44,168; and

Danny L. Williams, Reg. No. 31,892; Terry D. Morgan, Reg. No. 31,181; J. Mike Amerson, Reg. No. 35,426; Kenneth D. Goodman, Reg. No. 30,460; Barbara S. Kitchell, Reg. No. 33,928; Jeffrey A. Pyle, Reg. No. 34,904; Randall C. Furlong, Reg. No. 35,144; Scott F. Diring, Reg. No. 35,119; George J. Oehling, Reg. No. 40,471; Shelley P.M. Fussey, Reg. No. 39,458; Mark D. Moore, Reg. No. 42,903; Louis H. Iselin, Reg. No. 42,684; Raymund F. Eich, Reg. No. 42,508; Bradley A. Misley, Reg. No. 46,937; and Thomas H. Belvin, Jr., Reg. No. 43,491 of Williams, Morgan & Amerson, P.C.,

as its attorney or agent so long as they remain with such firms, with full power of substitution and revocation, to prosecute the application, to make alterations and amendments therein, to transact all business in the Patent and Trademark Office in connection therewith, and to receive any Letters Patent, and for one year after issuance of such Letters Patent to file any request for a certificate of correction that may be deemed appropriate.

Please direct all communications as follows:

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<u>J. Mike Amerson</u> WILLIAMS, MORGAN & AMERSON, P.C. 7676 Hillmont, Suite 250 Houston, Texas 77040 (713) 934-40<u>5</u>5

Signature: _	9. Millar	Date:	31-01-01	
	Gert Burbach			
Signature: _	Frank Temberin	_ Date:_	01-Feb-2001	
	Frank Heinlein			
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	Hartmut Ruelke		<i>,</i>	

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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Serial No.: Unknown

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	Johannes Groschopf	
Signature:	5. A hlandin	Date: 02/26/01
	Carste n Hartig	